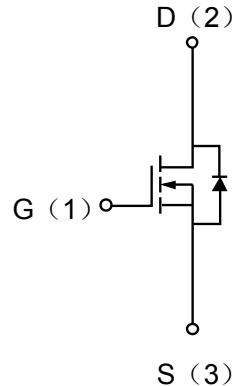


## Description

The enhancement mode MOS is extremely high density cell and low on-resistance.



MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
600	7.5@ V <sub>GS</sub> =10V	1.3

## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	600		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2		4	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.95A	-	7.5	9	Ω
Forward Tran conductance	g <sub>FS</sub>	V <sub>DS</sub> =0V, I <sub>D</sub> =0.65A		0.9		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.65	1	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				1	A
Maximum Body-Diode Pulse Current	I <sub>SM</sub>				4	A
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	105	130	160	pF
Output Capacitance	C <sub>OSS</sub>		12	14.5	17.5	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>		1.5	1.8	2.2	pF
<b>SWITCHING PARAMETERS</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> =300V, V <sub>GS</sub> =10V, R <sub>G</sub> =25Ω, I <sub>D</sub> =1A	-	10	13	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	20	26	ns
Turn-On Rise Time	t <sub>r</sub>			6.7	13	ns
Turn-Off Fall Time	t <sub>f</sub>			11.5	23	ns

**Absolute maximum rating@25°C**

Rating		Symbol	Value	Units
Drain-Source Voltage		$V_{DS}$	600	V
Gate-Source Voltage		$V_{GS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	1.3	A
	Pulsed	$I_D$	4.0	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	$P_D$	44	W
	$T_A=70^\circ\text{C}$	$P_D$	30	W

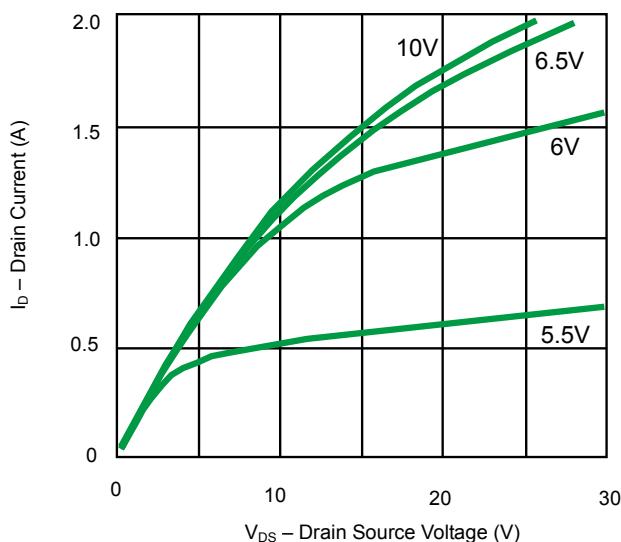
**Typical Characteristics**

Fig 1. On-Region Characteristics

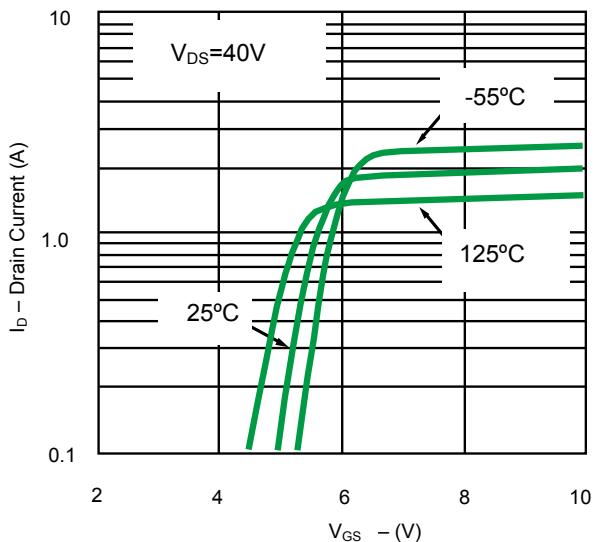


Fig 2. Transfer Characteristics

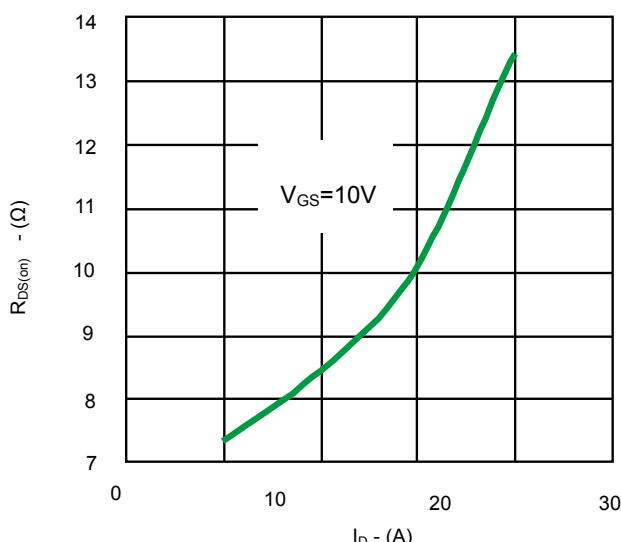


Fig 3. On-Resistance vs. Drain Current and Gate Voltage

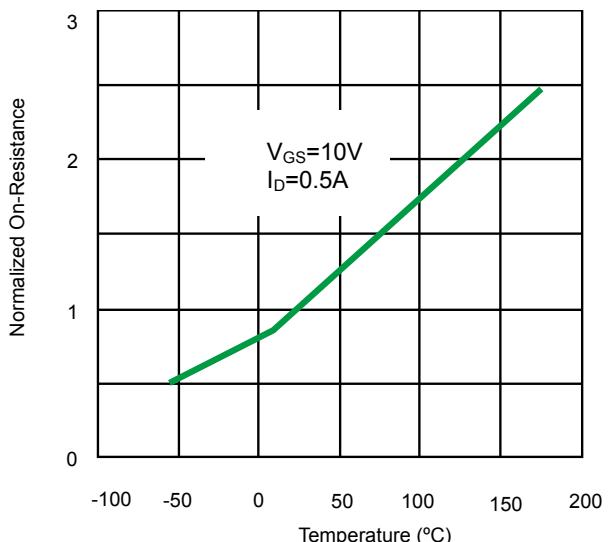
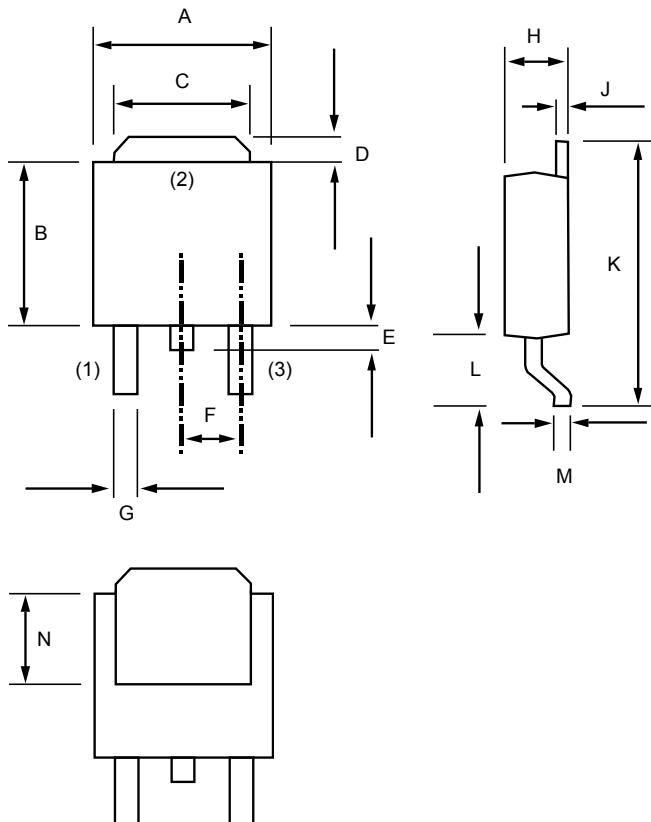


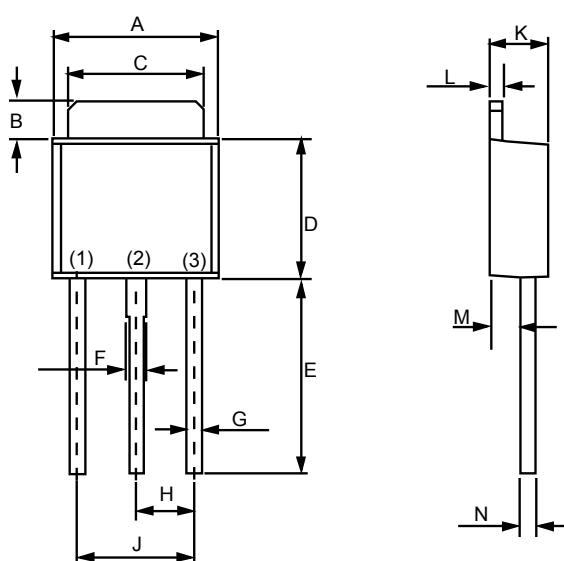
Fig 4. On-Resistance vs. Junction Temperature

## Product dimension(PNMDP600V1) (TO-252)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	6.350	6.650	0.250	0.262
B	5.400	5.700	0.213	0.224
C	5.200	5.400	0.205	0.213
D	1.350	1.650	0.053	0.065
E	-	1.01	-	0.040
F	2.300TYP		0.091TYP	
G	0.500	0.700	0.020	0.028
H	2.200	2.400	0.087	0.094
J	0.430	0.580	0.017	0.023
K	9.500	9.900	0.374	0.390
L	2.550	2.900	0.100	0.114
M	0.430	0.580	0.017	0.023
N	3.80REF		0.150REF	

## Product dimension(PNMP600V1) (TO-251)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	6.350	6.650	0.250	0.262
B	1.350	1.650	0.053	0.065
C	5.200	5.400	0.205	0.213
D	5.400	5.700	0.213	0.224
E	7.500	7.900	0.295	0.311
F	0.700	0.900	0.028	0.035
G	0.500	0.700	0.020	0.028
H	2.300 TYP		0.091 TYP	
J	4.500	4.700	0.177	0.185
K	2.200	2.400	0.087	0.094
L	0.430	0.580	0.017	0.023
M	1.020	1.270	0.040	0.050
N	0.430	0.580	0.017	0.023

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